

Single 2-Input NAND Gate

General Description

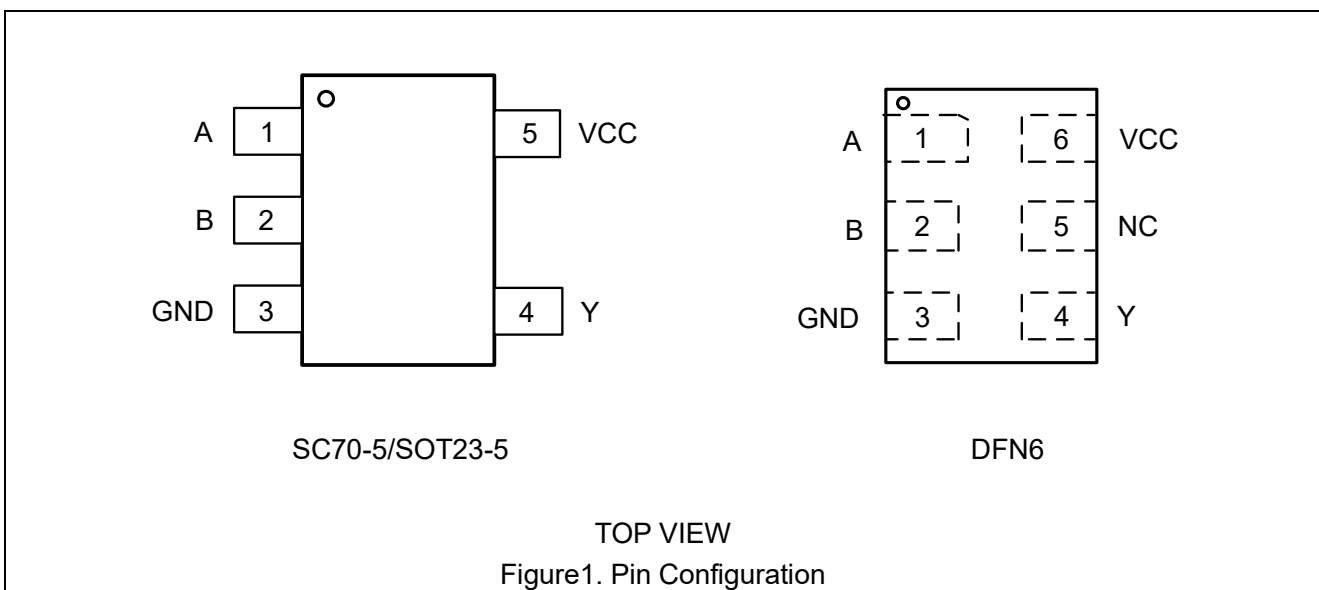
The ET74HC1G00 is a single 2-input NAND Gate operating from a 2V to 6V supply. This device is fabricated with advanced CMOS technology to achieve ultra-high speed with high output drive.

Features

- Designed for 2V to 6V V_{CC} Operation
- Over-voltage Tolerant Inputs
- 2.6mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- These Devices are Pb-Free and are RoHS Compliant
- ESD Protection Complies with JESD22 Standard
 - HBM: $\pm 4000V$ Pass (JEDEC JS-001)
 - CDM: $\pm 1000V$ Pass (JEDEC JS-002)
- Latch-up Performance Exceeds $\pm 100mA$ per JEDEC JESD78F
- Part No. and Package Information

Part No.	Package	Packing Option	MSL
ET74HC1G00	SC70-5 (1.3mm × 2.1mm)	Tape and Reel, 3K/Reel	Level 1
ET74HC1G00T	SOT23-5 (1.6mm × 2.9mm)	Tape and Reel, 3K/Reel	Level 3
ET74HC1G00Y	DFN6 (1.0mm × 1.5mm)	Tape and Reel, 3K/Reel	Level 1

Pin Configuration



ET74HC1G00

Pin Function

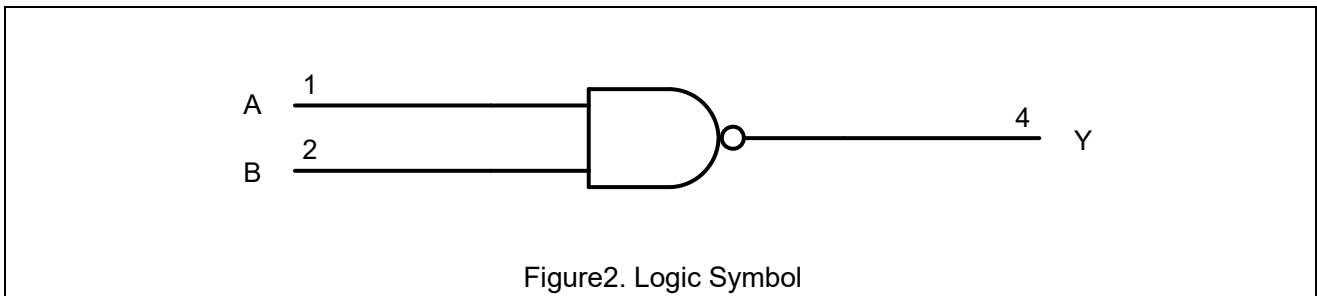
SC70-5 / SOT23-5

Pin No.	Pin Name	Function
1	A	Input A
2	B	Input B
3	GND	Ground
4	Y	Output Y
5	VCC	Supply Voltage

DFN6

Pin No.	Pin Name	Function
1	A	Input A
2	B	Input B
3	GND	Ground
4	Y	Output Y
5	NC	No Connect
6	VCC	Supply Voltage

Block Diagram



Function Table

Input		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

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Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage(V _{CC} Pin)		-0.5 to 7.0	V
V _I	DC Input Voltage ⁽¹⁾		-0.5 ≤ V _I ≤ +7.0	V
V _O	DC Output Voltage Output in Higher or Low State		-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current V _I < GND		-20	mA
I _{OK}	DC Output Diode Current V _O < GND, V _O > V _{CC}		±20	mA
I _O	DC Output Sink Current		±12.5	mA
I _{CC}	DC Supply Current Per Supply Pin		+25	mA
I _{GND}	DC Ground Current Per Supply Pin		-25	mA
T _{STG}	Storage Temperature Range		-65 to 150	°C
T _L	Lead Temperature, Soldering 10 Seconds		260	°C
T _J	Max Junction Temperature		150	°C
V _{ESD}	ESD Classification	Human Body Model ⁽²⁾	±4000	V
		Charged Device Model ⁽³⁾	±1000	
I _{LU}	Max Latch Up Current Above V _{CC} and GND at 125°C ⁽⁴⁾		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note1: I_O absolute maximum rating must be observed.

Note2: HBM tested per JEDEC JS-001;

Note3: CDM tested per JEDEC JS-002;

Note4: Latch Up Current Maximum Rating tested per JEDEC JESD78F.

Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
R _{θJA}	SC70-5	Thermal Characteristics, Thermal Resistance, Junction-to-Air	300	°C/W
	SOT23-5		250	
	DFN6		440	
P _D	SC70-5	Power Dissipation in Still Air at 85°C	215	mW
	SOT23-5		260	
	DFN6		150	

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Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage Operating	2	6	V
V _{IN}	DC Input Voltage	0	V _{CC}	V
V _{OUT}	DC Output Voltage (High or Low State)	0	V _{CC}	V
T _A	Operating Temperature Range	-40	15	°C

Electrical Characteristics

DC Electrical Characteristics

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25 °C			-40°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		2.0	1.5			1.5		V
			4.5	3.15			3.15		
			6.0	4.2			4.2		
V _{IL}	Low-Level Input Voltage		2.0			0.5		0.5	V
			4.5			1.35		1.35	
			6.0			1.8		1.8	
V _{OH}	High-Level Output Voltage	I _{OH} = -20uA	2~6	V _{CC} - 0.1	V _{CC}		V _{CC} - 0.1		V
		I _{OH} = -2mA	4.5	4.13	4.32		3.7		
		I _{OH} = -2.6mA	6.0	5.63	5.81		5.2		
V _{OL}	Low-Level Output Voltage	I _{OL} = 100uA	2~6		0.0	0.1		0.1	V
		I _{OL} = 2mA	4.5		0.15	0.33		0.4	
		I _{OL} = 2.6mA	6.0		0.16	0.33		0.4	
I _{IN}	Input Leakage Current	V _{IN} = 6V or GND	0~6			±0.1		±1.0	uA
I _{OFF}	Power Off Leakage Current	V _{IN} = 6V or V _{OUT} = 6V	0			1		10	uA
I _{CC}	Quiescent Supply Current	V _{IN} = 6V or GND	6			1		10	uA

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AC Electrical Characteristics

$t_r = t_f = 2.5\text{ns}$

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25 °C			-40°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay (Figure3 and 4)	C _L = 50pF	2.0		31	121		141	ns
		C _L = 50pF	4.5		11	25		29	
		C _L = 15pF	5.0		9				
		C _L = 50pF	6.0		10	23		26	

Capacitance Characteristics

Symbol	Parameter	Condition	Typ	Unit
C _{IN}	Input Capacitance	V _{CC} = 6V, V _I = 0V or V _{CC}	5	pF
C _{PD}	Power Dissipation Capacitance ⁽⁵⁾	10MHz, V _{CC} = 3.3V, V _I = 0V or V _{CC}	21	pF
		10MHz, V _{CC} = 6V, V _I = 0V or V _{CC}	21	

Note5. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

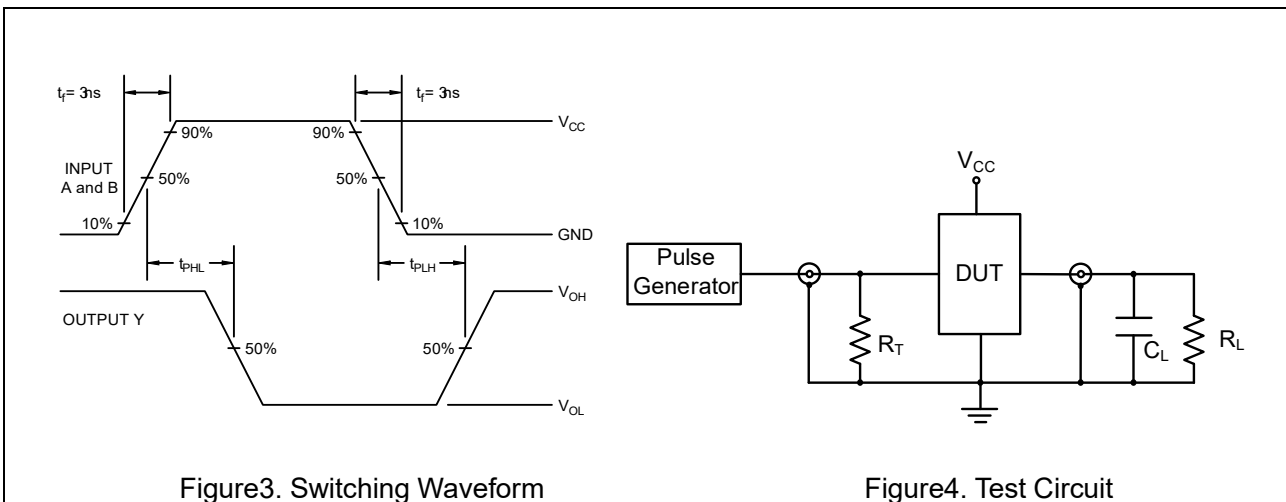
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

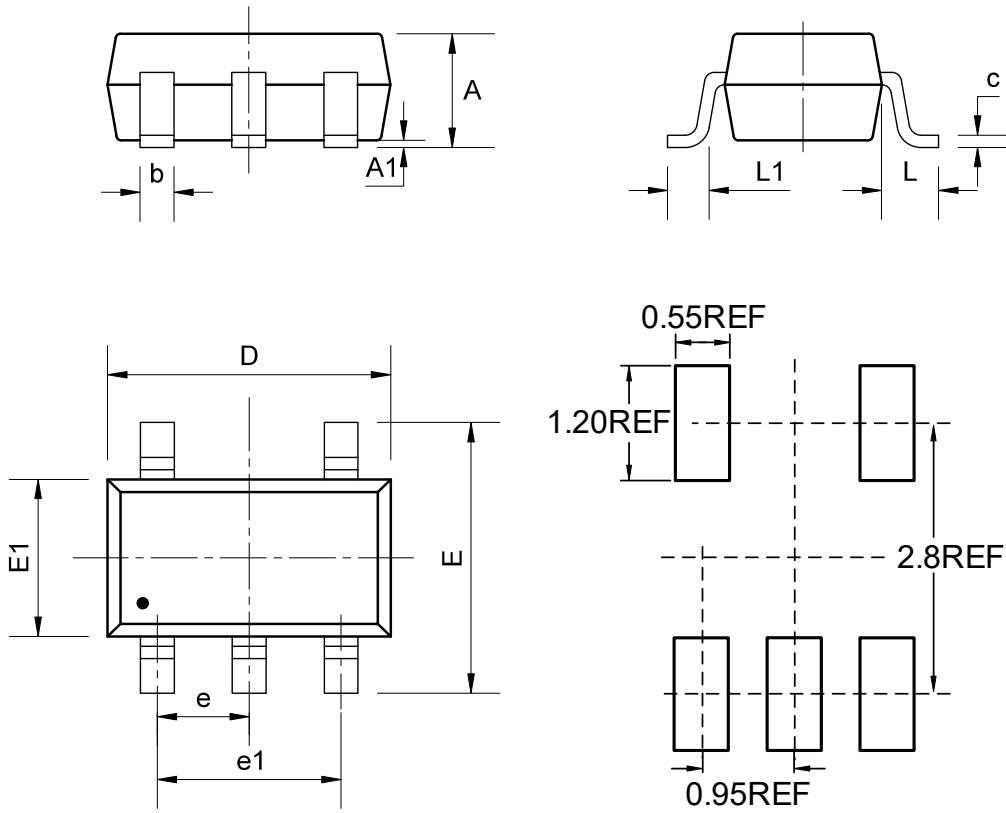
$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

AC Test Circuit



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SOT23-5 (1.6mm × 2.9mm)



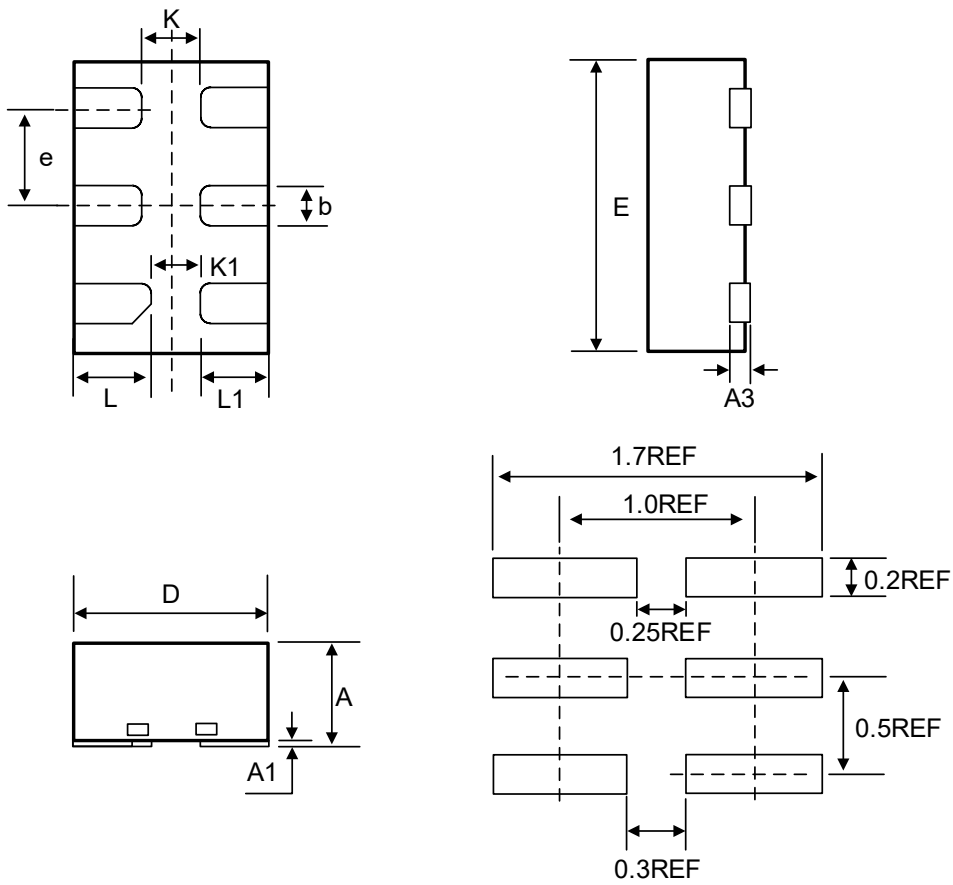
COMMON DIMENSIONS

(Unit: mm)

SYMBOL	MIN	NOM	MAX
A	-	-	1.25
A1	0.00	-	0.15
b	0.36	-	0.50
c	0.12	-	0.20
D	2.75	2.9	3.05
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
E	2.60	2.80	3.00
E1	1.45	1.6	1.75
L	0.60REF		
L1	0.30	0.45	0.60

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DFN6 (1.0mm × 1.5mm)



COMMON DIMENSIONS

(Unit: mm)

SYMBOL	MIN	NOM	MAX
A	0.50	--	0.60
A1	0.00	0.02	0.05
A3	0.10REF		
b	0.15	0.20	0.25
D	0.90	1.00	1.10
E	1.40	1.50	1.60
e	0.50BSC		
K	0.30REF		
K1	0.25REF		
L	0.35	0.40	0.45
L1	0.30	0.35	0.40

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Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2025-08-25	Official Version	Wang anran	Yang xiaoxu	Liu jiaoying